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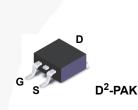
IRFW630B N-Channel MOSFET 200 V, 9 A, 400 mΩ

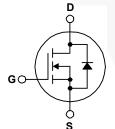
Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar, DMOS technology.This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supplies, DC-AC converters for uninterrupted power supply and motor control.

Features

- 9.0 A, 200 V, $R_{DS(on)}$ = 400 m Ω (Max.) @ V_{GS} = 10 V, I_D = 4.5 A
- Low Gate Charge (Typ. 22 nC)
- Low C_{rss} (Typ. 22 pF)
- 100% Avalanche Tested





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

| Symbol | Parameter | IRFW630BTM_FP001 | Unit |
|----------------------------------|---|------------------|------|
| V _{DSS} | Drain-Source Voltage | 200 | V |
| ID | Drain Current - Continuous (T _C = 25°C) | 9.0 | А |
| | - Continuous (T _C = 100°C) | 5.7 | А |
| I _{DM} | Drain Current - Pulsed (Note 1) | 36 | A |
| V _{GSS} | Gate-Source voltage | ± 30 | V |
| E _{AS} | Single Pulsed Avalanche Energy (Note 2) | 160 | mJ |
| I _{AR} | Avalanche Current (Note 1) | 9.0 | Α |
| E _{AR} | Repetitive Avalanche Energy (Note 1) | 7.2 | mJ |
| dv/dt | Peak Diode Recovery dv/dt (Note 3) | 5.5 | V/ns |
| P _D | Power Dissipation $(T_A = 25^{\circ}C)^*$ | 3.13 | W |
| | Power Dissipation $(T_C = 25^{\circ}C)$ | 72 | W |
| | - Derate above 25°C | 0.57 | W/°C |
| T _{J,} T _{STG} | Operating and Storage Temperature Range | -55 to +150 | °C |
| Τ _L | Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds | 300 | °C |

Thermal Characteristics

| Symbol | Parameter | IRFW630BTM_FP001 | Unit | |
|----------------|---|------------------|------|--|
| R_{\thetaJC} | Thermal Resistance, Junction to Case, Max. | 1.74 | | |
| $R_{	heta JA}$ | Thermal Resistance, Junction to Ambient (Min. Pad of 2-oz Copper), Max. | 62.5 | °C/W | |
| | Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max. | 40 | | |

| Device Marking Device | | Package Reel Size | | T | ape Widtl | n Qu | uantity | |
|---|--|--------------------------------------|---|----------|-----------|------|---------|------|
| IRFW630B IRFW630BTM_FP001 | | D ² -PAK | 330 mm | | 24 mm | 80 | 0 units | |
| Electric | al Cha | racteristics T _c =25°C un | less otherwise noted. | | | | | |
| Symbol | | Parameter | Condi | tions | Min | Тур | Max | Unit |
| Off Charac | teristics | | | | | | | |
| BV _{DSS} | Drain-Source Breakdown Voltage | | V _{GS} = 0 V, I _D = 250 μA | | 200 | | | V |
| ΔΒV _{DSS} / ΔT _J | Breakdown Voltage Temperature Coefficient | | $I_D = 250 \ \mu$ A, Referenced to 25°C | | | 0.2 | | V/ºC |
| I _{DSS} | Zero Gate Voltage Drain Current | | V _{DS} = 200 V, V _{GS} | = 0 V | | | 10 | μA |
| | | | V _{DS} = 160 V, T _C = 125°C | | | | 100 | μA |
| I _{GSSF} | Gate-Boo | ly Leakage Current, Forward | V _{GS} = 30 V, V _{DS} = | = 0 V | | | 100 | nA |
| I _{GSSR} | Gate-Body Leakage Current, Reverse | | V _{GS} = -30 V, V _{DS} = 0 V | | | | -100 | nA |
| On Charac | teristics | | | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | | $V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$ | | 2.0 | | 4.0 | V |
| R _{DS(on)} | Static Drain-Source On-Resistance | | V _{GS} = 10 V, I _D = 4.5 A | | | 0.34 | 0.4 | Ω |
| 9 _{FS} | Forward Transconductance | | V _{DS} = 40 V, I _D = 4.5 A | | | 7.05 | | S |
| Dynamic C | haracteris | stics | | | | | | |
| C _{iss} | Input Cap | pacitance | V _{DS} = 25 V, V _{GS} = 0 V, f = 1.0 MHz | | - | 550 | 720 | pF |
| C _{oss} | Output C | apacitance | | | | 85 | 110 | pF |
| C _{rss} | Reverse | Transfer Capacitance | | | | 22 | 29 | pF |
| Switching | Character | istics | | | | | | |
| t _{d(on)} | Turn-On Delay Time | | V _{DD} = 100 V, I _D = 9.0 A | | 11 | 30 | ns | |
| t _r | Turn-On | Rise Time | R _G = 25 Ω | | | 70 | 150 | ns |
| t _{d(off)} | Turn-Off | Delay Time | | | | 60 | 130 | ns |
| t _f | Turn-Off | Fall Time | | (Note 4) | | 65 | 140 | ns |
| Qg | Total Gat | e Charge | V _{DS} = 160 V, I _D = | 9.0 A | | 22 | 29 | nC |
| Q _{gs} | Gate-Sou | Irce Charge | V _{GS} = 10 V (Note 4) | | | 3.6 | | nC |
| Q _{gd} | Gate-Dra | in Charge | | | | 10.2 | | nC |
| Drain-Sou | rce Diode | Characteristics and Maximu | m Ratings | | -/ | | | |
| I _S | Maximum Continuous Drain-Source Did | | ode Forward Current | | | | 9.0 | А |
| I _{SM} | Maximum Pulsed Drain-Source Diode I | | Forward Current | | | | 36 | Α |
| V _{SD} | Drain-So | urce Diode Forward Voltage | V _{GS} = 0 V, I _S = 9.0 | | | | 1.5 | V |
| t _{rr} | Reverse | Recovery Time | $V_{GS} = 0 V, I_{S} = 9.0$ | A C | | 140 | | ns |
| Q _{rr} | Reverse | Recovery Charge | dl _F /dt =100 A/μs | | | 0.87 | | μC |

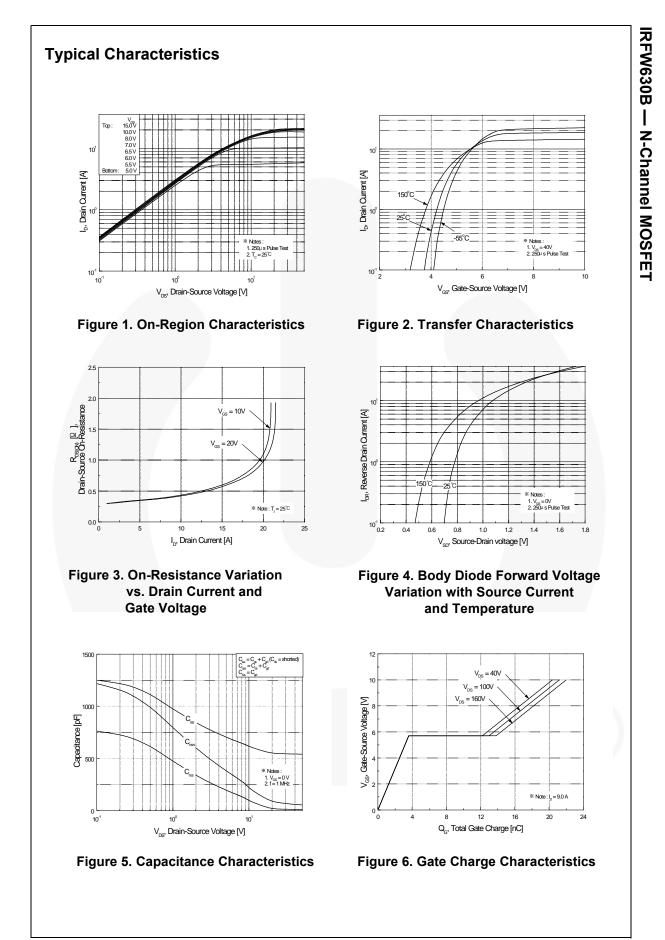
Notes:

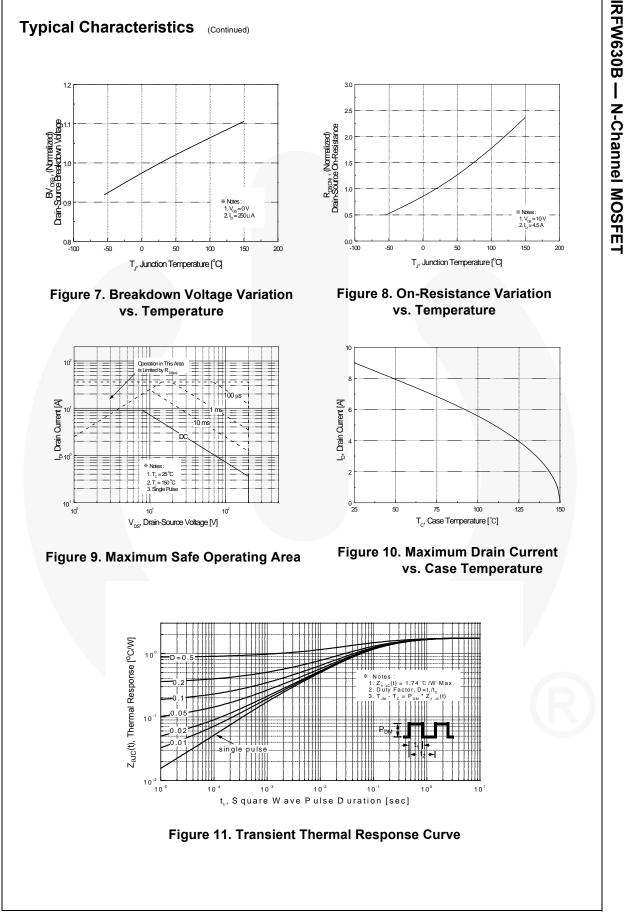
1. Repetitive rating: pulse-width limited by maximum junction temperature.

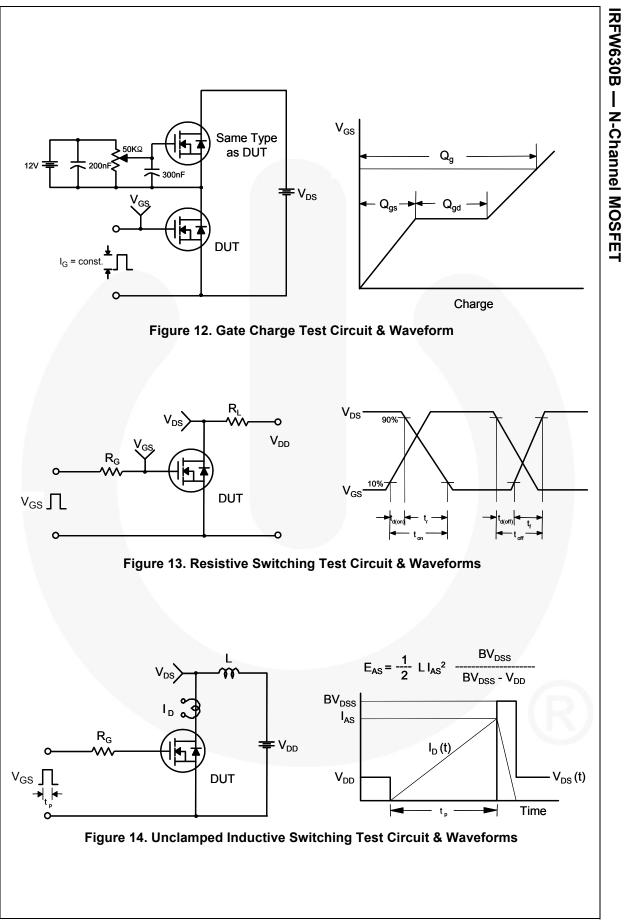
2. L = 3 mH, I_{AS} = 9.0 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.

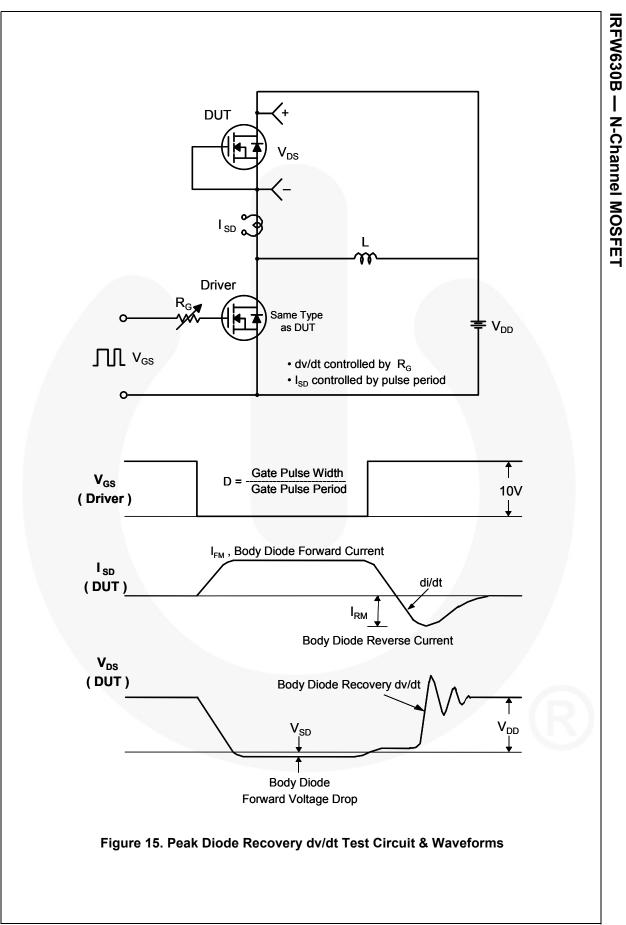
3. I_{SD} \leq 9.0 A, di/dt \leq 300 A/µs, V_{DD} \leq BV_{DSS,} starting ~T_J = 25°C.

4. Essentially independent of operating temperature.











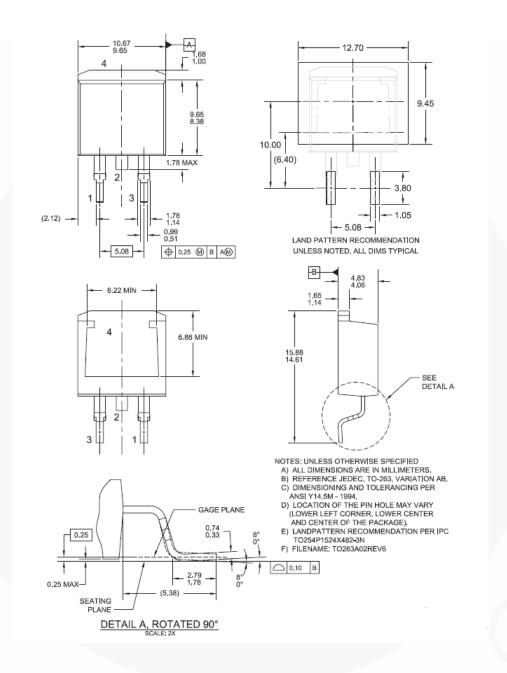


Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

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